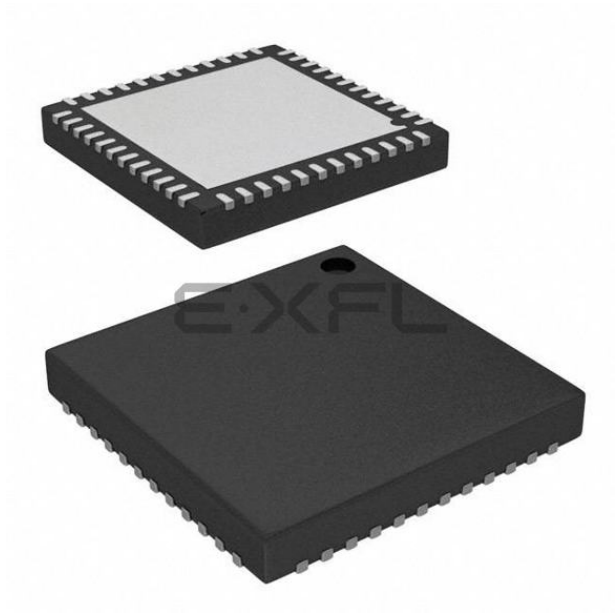

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	8051
Core Size	8-Bit
Speed	50MHz
Connectivity	EBI/EMI, I²C, LINbus, SPI, UART/USART, USB
Peripherals	CapSense, DMA, POR, PWM, WDT
Number of I/O	25
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	1K x 8
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 5.5V
Data Converters	A/D 16x12b; D/A 1x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-VFQFN Exposed Pad
Supplier Device Package	48-QFN (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/cy8c3245lti-144t

In addition to the flexibility of the UDB array, PSoC also provides configurable digital blocks targeted at specific functions. For the CY8C32 family these blocks can include four 16-bit timers, counters, and PWM blocks; I^2C slave, master, and multimaster; and FS USB.

For more details on the peripherals see the "Example Peripherals" section on page 45 of this datasheet. For information on UDBs, DSI, and other digital blocks, see the "Digital Subsystem" section on page 45 of this datasheet.

PSoC's analog subsystem is the second half of its unique configurability. All analog performance is based on a highly accurate absolute voltage reference with less than 1-percent error over temperature and voltage. The configurable analog subsystem includes:

- Analog muxes
- Comparators
- Voltage references
- ADC
- DAC

All GPIO pins can route analog signals into and out of the device using the internal analog bus. This allows the device to interface up to 62 discrete analog signals. The heart of the analog subsystem is a fast, accurate, configurable delta-sigma ADC with these features:

- Less than 100 µV offset
- A gain error of 0.2 percent
- INL less than ±1 LSB
- DNL less than ±1 LSB
- SINAD better than 66 dB

This converter addresses a wide variety of precision analog applications, including some of the most demanding sensors.

A high-speed voltage or current DAC supports 8-bit output signals at an update rate of 8 Msps in current DAC (IDAC) and 1 Msps in voltage DAC (VDAC). It can be routed out of any GPIO pin. You can create higher resolution voltage PWM DAC outputs using the UDB array. This can be used to create a pulse width modulated (PWM) DAC of up to 10 bits, at up to 48 kHz. The digital DACs in each UDB support PWM, PRS, or delta-sigma algorithms with programmable widths.

In addition to the ADC and DAC, the analog subsystem provides multiple comparators.

See the "Analog Subsystem" section on page 55 of this datasheet for more details.

PSoC's 8051 CPU subsystem is built around a single cycle pipelined 8051 8-bit processor running at up to 50 MHz. The CPU subsystem includes a programmable nested vector interrupt controller, DMA controller, and RAM. PSoC's nested vector interrupt controller provides low latency by allowing the CPU to vector directly to the first address of the interrupt service routine, bypassing the jump instruction required by other architectures. The DMA controller enables peripherals to exchange data without CPU involvement. This allows the CPU to run slower (saving power) or use those CPU cycles to improve the performance of firmware algorithms. The single cycle 8051 CPU runs ten times faster than a standard 8051 processor. The processor speed itself is configurable, allowing you to tune active power consumption for specific applications.

PSoC's nonvolatile subsystem consists of flash, byte-writeable EEPROM, and nonvolatile configuration options. It provides up to 64 KB of on-chip flash. The CPU can reprogram individual blocks of flash, enabling bootloaders. You can enable an ECC for high reliability applications. A powerful and flexible protection model secures the user's sensitive information, allowing selective memory block locking for read and write protection. Up to 2 KB of byte-writeable EEPROM is available on-chip to store application data. Additionally, selected configuration options such as boot speed and pin drive mode are stored in nonvolatile memory. This allows settings to activate immediately after POR.

The three types of PSoC I/O are extremely flexible. All I/Os have many drive modes that are set at POR. PSoC also provides up to four I/O voltage domains through the VDDIO pins. Every GPIO has analog I/O, LCD drive[3], CapSense[4], flexible interrupt generation, slew rate control, and digital I/O capability. The SIOs on PSoC allow Voh to be set independently of VDDIO when used as outputs. When SIOs are in input mode they are high impedance. This is true even when the device is not powered or when the pin voltage goes above the supply voltage. This makes the SIO ideally suited for use on an I^2C bus where the PSoC may not be powered when other devices on the bus are. The SIO pins also have high current sink capability for applications such as LED drives. The programmable input threshold feature of the SIO can be used to make the SIO function as a general purpose analog comparator. For devices with FS USB the USB physical interface is also provided (USBIO). When not using USB these pins may also be used for limited digital functionality and device programming. All of the features of the PSoC I/Os are covered in detail in the "I/O System and Routing" section on page 37 of this datasheet.

The PSoC device incorporates flexible internal clock generators, designed for high stability and factory trimmed for high accuracy. The Internal Main Oscillator (IMO) is the clock base for the system, and has 2-percent accuracy at 3 MHz. The IMO can be configured to run from 3 MHz up to 24 MHz. Multiple clock derivatives can be generated from the main clock frequency to meet application needs. The device provides a PLL to generate clock frequencies up to 50 MHz from the IMO, external crystal, or external reference clock. It also contains a separate, very low-power Internal Low-Speed Oscillator (ILO) for the sleep and watchdog timers. A 32.768-kHz external watch crystal is also supported for use in RTC applications. The clocks, together with programmable clock dividers, provide the flexibility to integrate most timing requirements.

The CY8C32 family supports a wide supply operating range from 1.71 V to 5.5 V. This allows operation from regulated supplies such as 1.8 ± 5 percent, 2.5 V ±10 percent, 3.3 V ± 10 percent, or 5.0 V ± 10 percent, or directly from a wide range of battery types. In addition, it provides an integrated high efficiency synchronous boost converter that can power the device from supply voltages as low as 0.5 V.

Notes
3. This feature on select devices only. See Ordering Information on page 111 for details.
4. GPIOs with opamp outputs are not recommended for use with CapSense.

4.4.4.5 Scatter Gather DMA

In the case of scatter gather DMA, there are multiple noncontiguous sources or destinations that are required to effectively carry out an overall DMA transaction. For example, a packet may need to be transmitted off of the device and the packet elements, including the header, payload, and trailer, exist in various noncontiguous locations in memory. Scatter gather DMA allows the segments to be concatenated together by using multiple TDs in a chain. The chain gathers the data from the multiple locations. A similar concept applies for the reception of data onto the device. Certain parts of the received data may need to be scattered to various locations in memory for software processing convenience. Each TD in the chain specifies the location for each discrete element in the chain.

4.4.4.6 Packet Queuing DMA

Packet queuing DMA is similar to scatter gather DMA but specifically refers to packet protocols. With these protocols, there may be separate configuration, data, and status phases associated with sending or receiving a packet.

For instance, to transmit a packet, a memory mapped configuration register can be written inside a peripheral, specifying the overall length of the ensuing data phase. The CPU can set up this configuration information anywhere in system memory and copy it with a simple TD to the peripheral. After the configuration phase, a data phase TD (or a series of data phase TDs) can begin (potentially using scatter gather). When the data phase TD(s) finish, a status phase TD can be invoked that reads some memory mapped status information from the peripheral and copies it to a location in system memory specified by the CPU for later inspection. Multiple sets of configuration, data, and status phase “subchains” can be strung together to create larger chains that transmit multiple packets in this way. A similar concept exists in the opposite direction to receive the packets.

4.4.4.7 Nested DMA

One TD may modify another TD, as the TD configuration space is memory mapped similar to any other peripheral. For example, a first TD loads a second TD’s configuration and then calls the second TD. The second TD moves data as required by the application. When complete, the second TD calls the first TD, which again updates the second TD’s configuration. This process repeats as often as necessary.

4.5 Interrupt Controller

The interrupt controller provides a mechanism for hardware resources to change program execution to a new address, independent of the current task being executed by the main code. The interrupt controller provides enhanced features not found on original 8051 interrupt controllers:

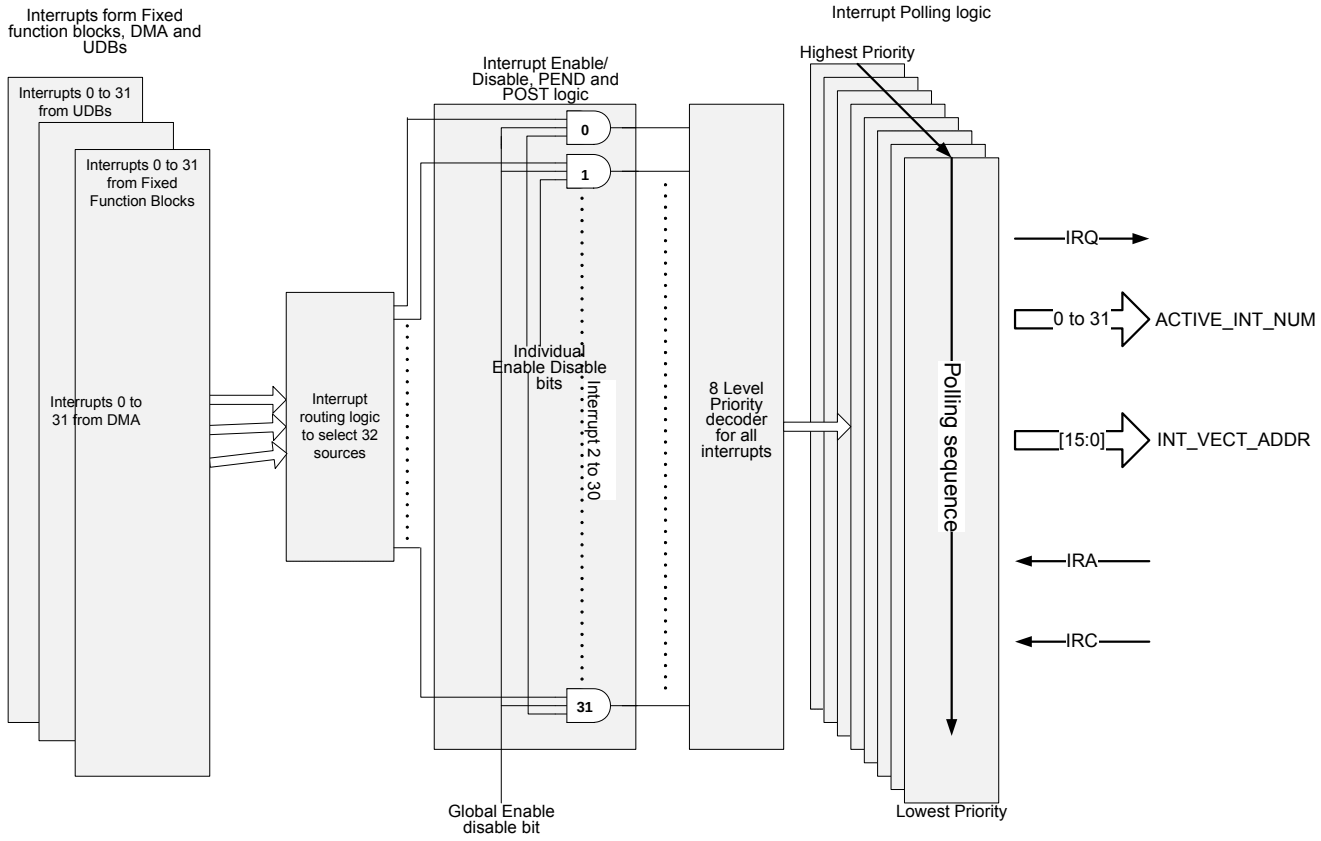
- Thirty two interrupt vectors
- Jumps directly to ISR anywhere in code space with dynamic vector addresses
- Multiple sources for each vector
- Flexible interrupt to vector matching
- Each interrupt vector is independently enabled or disabled
- Each interrupt can be dynamically assigned one of eight priorities
- Eight level nestable interrupts
- Multiple I/O interrupt vectors
- Software can send interrupts
- Software can clear pending interrupts

When an interrupt is pending, the current instruction is completed and the program counter is pushed onto the stack. Code execution then jumps to the program address provided by the vector. After the ISR is completed, a RETI instruction is executed and returns execution to the instruction following the previously interrupted instruction. To do this the RETI instruction pops the program counter from the stack.

If the same priority level is assigned to two or more interrupts, the interrupt with the lower vector number is executed first. Each interrupt vector may choose from three interrupt sources: Fixed Function, DMA, and UDB. The fixed function interrupts are direct connections to the most common interrupt sources and provide the lowest resource cost connection. The DMA interrupt sources provide direct connections to the two DMA interrupt sources provided per DMA channel. The third interrupt source for vectors is from the UDB digital routing array. This allows any digital signal available to the UDB array to be used as an interrupt source. Fixed function interrupts and all interrupt sources may be routed to any interrupt vector using the UDB interrupt source connections.

Figure 4-2 on page 21 represents typical flow of events when an interrupt triggered. Figure 4-3 on page 22 shows the interrupt structure and priority polling.

Figure 4-3. Interrupt Structure



5.5 Nonvolatile Latches (NVLs)

PSoC has a 4-byte array of nonvolatile latches (NVLs) that are used to configure the device at reset. The NVL register map is shown in Table 5-2.

Table 5-2. Device Configuration NVL Register Map

Register Address	7	6	5	4	3	2	1	0
0x00	PRT3RDM[1:0]		PRT2RDM[1:0]		PRT1RDM[1:0]		PRT0RDM[1:0]	
0x01	PRT12RDM[1:0]		PRT6RDM[1:0]		PRT5RDM[1:0]		PRT4RDM[1:0]	
0x02	XRESMEN	DBGEN					PRT15RDM[1:0]	
0x03	DIG_PHS_DLY[3:0]				ECCEN	DPS[1:0]		

The details for individual fields and their factory default settings are shown in Table 5-3:.

Table 5-3. Fields and Factory Default Settings

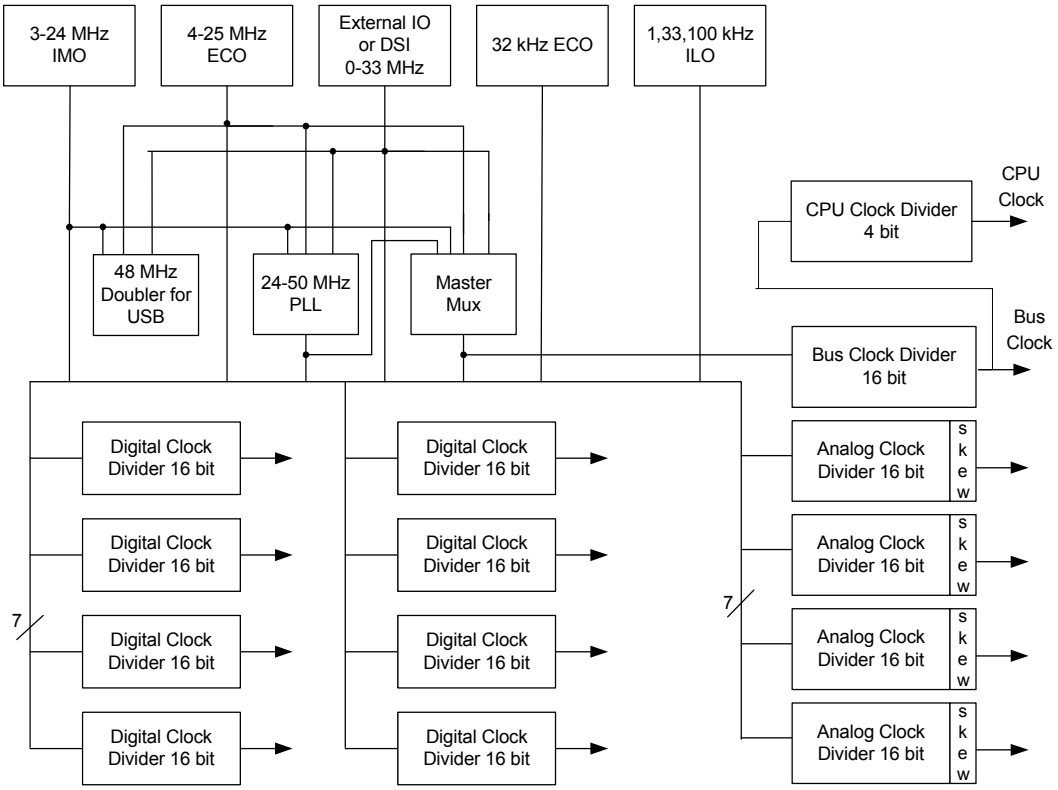
Field	Description	Settings
PRTxRDM[1:0]	Controls reset drive mode of the corresponding IO port. See "Reset Configuration" on page 44. All pins of the port are set to the same mode.	00b (default) - high impedance analog 01b - high impedance digital 10b - resistive pull up 11b - resistive pull down
XRESMEN	Controls whether pin P1[2] is used as a GPIO or as an external reset. See "Pin Descriptions" on page 12, XRES description.	0 (default for 68-pin 72-pin, and 100-pin parts) - GPIO 1 (default for 48-pin parts) - external reset
DBGEN	Debug Enable allows access to the debug system, for third-party programmers.	0 - access disabled 1 (default) - access enabled
DPS[1:0]	Controls the usage of various P1 pins as a debug port. See "Programming, Debug Interfaces, Resources" on page 62.	00b - 5-wire JTAG 01b (default) - 4-wire JTAG 10b - SWD 11b - debug ports disabled
ECCEN	Controls whether ECC flash is used for ECC or for general configuration and data storage. See "Flash Program Memory" on page 24.	0 - ECC disabled 1 (default) - ECC enabled
DIG_PHS_DLY[3:0]	Selects the digital clock phase delay.	See the TRM for details.

Although PSoC Creator provides support for modifying the device configuration NVLs, the number of NVL erase / write cycles is limited – see "Nonvolatile Latches (NVL))" on page 100.

Table 6-1. Oscillator Summary

Source	Fmin	Tolerance at Fmin	Fmax	Tolerance at Fmax	Startup Time
IMO	3 MHz	±2% over voltage and temperature	24 MHz	±4%	13-µs max
MHzECO	4 MHz	Crystal dependent	25 MHz	Crystal dependent	5 ms typ, max is crystal dependent
DSI	0 MHz	Input dependent	33 MHz	Input dependent	Input dependent
PLL	24 MHz	Input dependent	50 MHz	Input dependent	250 µs max
Doubler	48 MHz	Input dependent	48 MHz	Input dependent	1 µs max
ILO	1 kHz	–50%, +100%	100 kHz	–55%, +100%	15 ms max in lowest power mode
kHzECO	32 kHz	Crystal dependent	32 kHz	Crystal dependent	500 ms typ, max is crystal dependent

Figure 6-1. Clocking Subsystem



6.2.1 Power Modes

PSoC 3 devices have four different power modes, as shown in Table 6-2 and Table 6-3. The power modes allow a design to easily provide required functionality and processing power while simultaneously minimizing power consumption and maximizing battery life in low-power and portable devices.

PSoC 3 power modes, in order of decreasing power consumption are:

- Active
- Alternate Active
- Sleep
- Hibernate

Active is the main processing mode. Its functionality is configurable. Each power controllable subsystem is enabled or disabled by using separate power configuration template registers. In alternate active mode, fewer subsystems are enabled, reducing power. In sleep mode most resources are disabled regardless of the template settings. Sleep mode is optimized to provide timed sleep intervals and RTC functionality. The lowest power mode is hibernate, which retains register and SRAM state, but no clocks, and allows wakeup only from I/O pins. Figure 6-5 illustrates the allowable transitions between power modes. Sleep and hibernate modes should not be entered until all VDDIO supplies are at valid voltage levels.

Table 6-2. Power Modes

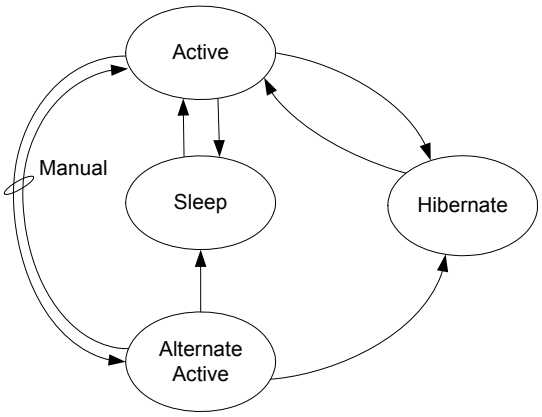
Power Modes	Description	Entry Condition	Wakeup Source	Active Clocks	Regulator
Active	Primary mode of operation, all peripherals available (programmable)	Wakeup, reset, manual register entry	Any interrupt	Any (programmable)	All regulators available. Digital and analog regulators can be disabled if external regulation used.
Alternate Active	Similar to Active mode, and is typically configured to have fewer peripherals active to reduce power. One possible configuration is to use the UDBs for processing, with the CPU turned off	Manual register entry	Any interrupt	Any (programmable)	All regulators available. Digital and analog regulators can be disabled if external regulation used.
Sleep	All subsystems automatically disabled	Manual register entry	Comparator, PICU, I^2C, RTC, CTW, LVD	ILO/kHzECO	Both digital and analog regulators buzzed. Digital and analog regulators can be disabled if external regulation used.
Hibernate	All subsystems automatically disabled Lowest power consuming mode with all peripherals and internal regulators disabled, except hibernate regulator is enabled Configuration and memory contents retained	Manual register entry	PICU		Only hibernate regulator active.

Table 6-3. Power Modes Wakeup Time and Power Consumption

Sleep Modes	Wakeup Time	Current (typ)	Code Execution	Digital Resources	Analog Resources	Clock Sources Available	Wakeup Sources	Reset Sources
Active	–	1.2 mA[11]	Yes	All	All	All	–	All
Alternate Active	–	–	User defined	All	All	All	–	All
Sleep	<15 µs	1 µA	No	I^2C	Comparator	ILO/kHzECO	Comparator, PICU, I^2C, RTC, CTW, LVD	XRES, LVD, WDR
Hibernate	<100 µs	200 nA	No	None	None	None	PICU	XRES

Note
11. Bus clock off. Execute from cache at 6 MHz. See Table 11-2 on page 68.

Figure 6-5. Power Mode Transitions



6.2.1.1 Active Mode

Active mode is the primary operating mode of the device. When in active mode, the active configuration template bits control which available resources are enabled or disabled. When a resource is disabled, the digital clocks are gated, analog bias currents are disabled, and leakage currents are reduced as appropriate. User firmware can dynamically control subsystem power by setting and clearing bits in the active configuration template. The CPU can disable itself, in which case the CPU is automatically reenabled at the next wakeup event.

When a wakeup event occurs, the global mode is always returned to active, and the CPU is automatically enabled, regardless of its template settings. Active mode is the default global power mode upon boot.

6.2.1.2 Alternate Active Mode

Alternate Active mode is very similar to Active mode. In alternate active mode, fewer subsystems are enabled, to reduce power consumption. One possible configuration is to turn off the CPU and flash, and run peripherals at full speed.

6.2.1.3 Sleep Mode

Sleep mode reduces power consumption when a resume time of 15 µs is acceptable. The wake time is used to ensure that the regulator outputs are stable enough to directly enter active mode.

6.2.1.4 Hibernate Mode

In hibernate mode nearly all of the internal functions are disabled. Internal voltages are reduced to the minimal level to keep vital systems alive. Configuration state is preserved in hibernate mode and SRAM memory is retained. GPIOs configured as digital outputs maintain their previous values and external GPIO pin interrupt settings are preserved. The device can only return from hibernate mode in response to an external I/O interrupt. The resume time from hibernate mode is less than 100 µs.

To achieve an extremely low current, the hibernate regulator has limited capacity. This limits the frequency of any signal present on the input pins - no GPIO should toggle at a rate greater than 10 kHz while in hibernate mode. If pins must be toggled at a high rate while in a low power mode, use sleep mode instead.

6.2.1.5 Wakeup Events

Wakeup events are configurable and can come from an interrupt or device reset. A wakeup event restores the system to active mode. Firmware enabled interrupt sources include internally generated interrupts, power supervisor, central timewheel, and I/O interrupts. Internal interrupt sources can come from a variety of peripherals, such as analog comparators and UDBs. The central timewheel provides periodic interrupts to allow the system to wake up, poll peripherals, or perform real-time functions. Reset event sources include the external reset I/O pin (XRES), WDT, and Precision Reset (PRES).

6.2.2 Boost Converter

Applications that use a supply voltage of less than 1.71 V, such as solar panels or single cell battery supplies, may use the on-chip boost converter to generate a minimum of 1.8 V supply voltage. The boost converter may also be used in any system that requires a higher operating voltage than the supply provides such as driving 5.0 V LCD glass in a 3.3 V system. With the addition of an inductor, Schottky diode, and capacitors, it produces a selectable output voltage sourcing enough current to operate the PSoC and other on-board components.

The boost converter accepts an input voltage V_{BAT} from 0.5 V to 3.6 V, and can start up with V_{BAT} as low as 0.5 V. The converter provides a user configurable output voltage of 1.8 to 5.0 V (V_{OUT}) in 100 mV increments. V_{BAT} is typically less than V_{OUT}; if V_{BAT} is greater than or equal to V_{OUT}, then V_{OUT} will be slightly less than V_{BAT} due to resistive losses in the boost converter. The block can deliver up to 50 mA (I_{BOOST}) depending on configuration to both the PSoC device and external components. The sum of all current sinks in the design including the PSoC device, PSoC I/O pin loads, and external component loads must be less than the I_{BOOST} specified maximum current.

Four pins are associated with the boost converter: VBAT, VSSB, VBOOST, and IND. The boosted output voltage is sensed at the VBOOST pin and must be connected directly to the chip's supply inputs, VDDA, VDDD, and VDDIO, if used to power the PSoC device.

The boost converter requires four components in addition to those required in a non-boost design, as shown in Figure 6-6 on page 35. A 22-µF capacitor (CBAT) is required close to the VBAT pin to provide local bulk storage of the battery voltage and provide regulator stability. A diode between the battery and VBAT pin should not be used for reverse polarity protection because the diodes forward voltage drop reduces the V_{BAT} voltage. Between the VBAT and IND pins, an inductor of 4.7 µH, 10 µH, or 22 µH is required. The inductor value can be optimized to increase the boost converter efficiency based on input voltage, output voltage, temperature, and current. Inductor size is determined by following the design guidance in this section and the electrical specifications. The inductor must be placed within 1 cm of the VBAT and IND pins and have a minimum saturation current of 750 mA. Between the IND and VBOOST pins, place a Schottky diode within 1 cm of the pins. This diode shall have a forward current rating of at least 1.0 A and a reverse voltage of at least 20 V. Connect a 22-µF bulk capacitor (CBOOST) close to VBOOST to provide regulator output stability. It is important to sum the total capacitance connected to the VBOOST pin and ensure the maximum CBOOST specification is not exceeded. All capacitors must be rated for a minimum of 10 V to minimize capacitive losses due to voltage de-rating.

Figure 6-10. SIO Input/Output Block Diagram

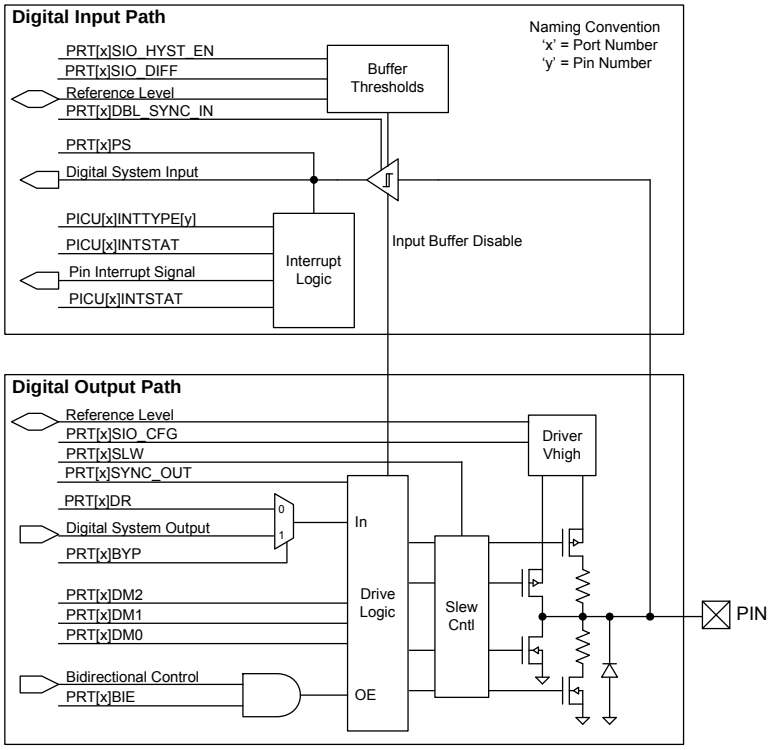
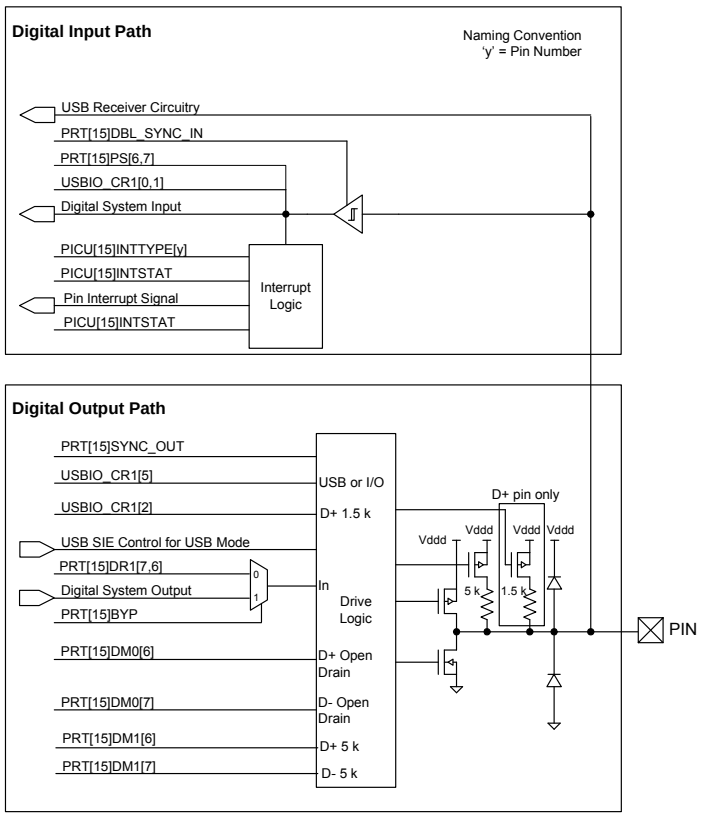


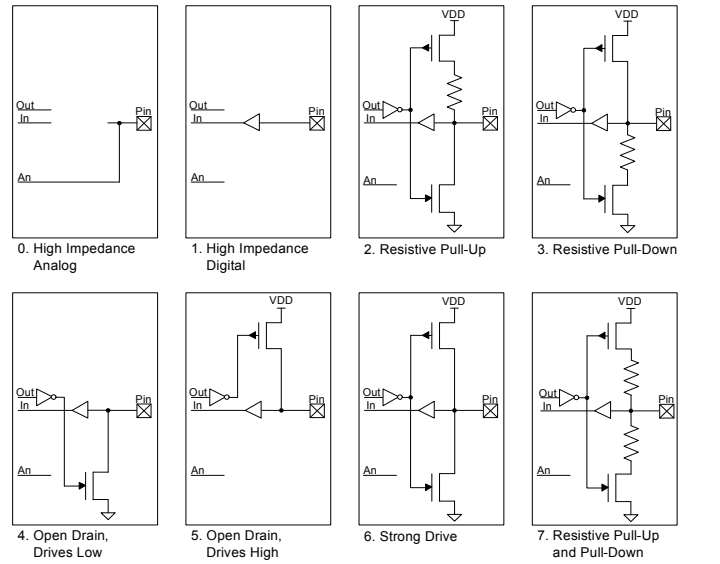
Figure 6-11. USBIO Block Diagram



6.4.1 Drive Modes

Each GPIO and SIO pin is individually configurable into one of the eight drive modes listed in Table 6-6. Three configuration bits are used for each pin (DM[2:0]) and set in the PRTxDM[2:0] registers. Figure 6-12 depicts a simplified pin view based on each of the eight drive modes. Table 6-6 shows the I/O pin's drive state based on the port data register value or digital array signal if bypass mode is selected. Note that the actual I/O pin voltage is determined by a combination of the selected drive mode and the load at the pin. For example, if a GPIO pin is configured for resistive pull-up mode and driven high while the pin is floating, the voltage measured at the pin is a high logic state. If the same GPIO pin is externally tied to ground then the voltage unmeasured at the pin is a low logic state.

Figure 6-12. Drive Mode



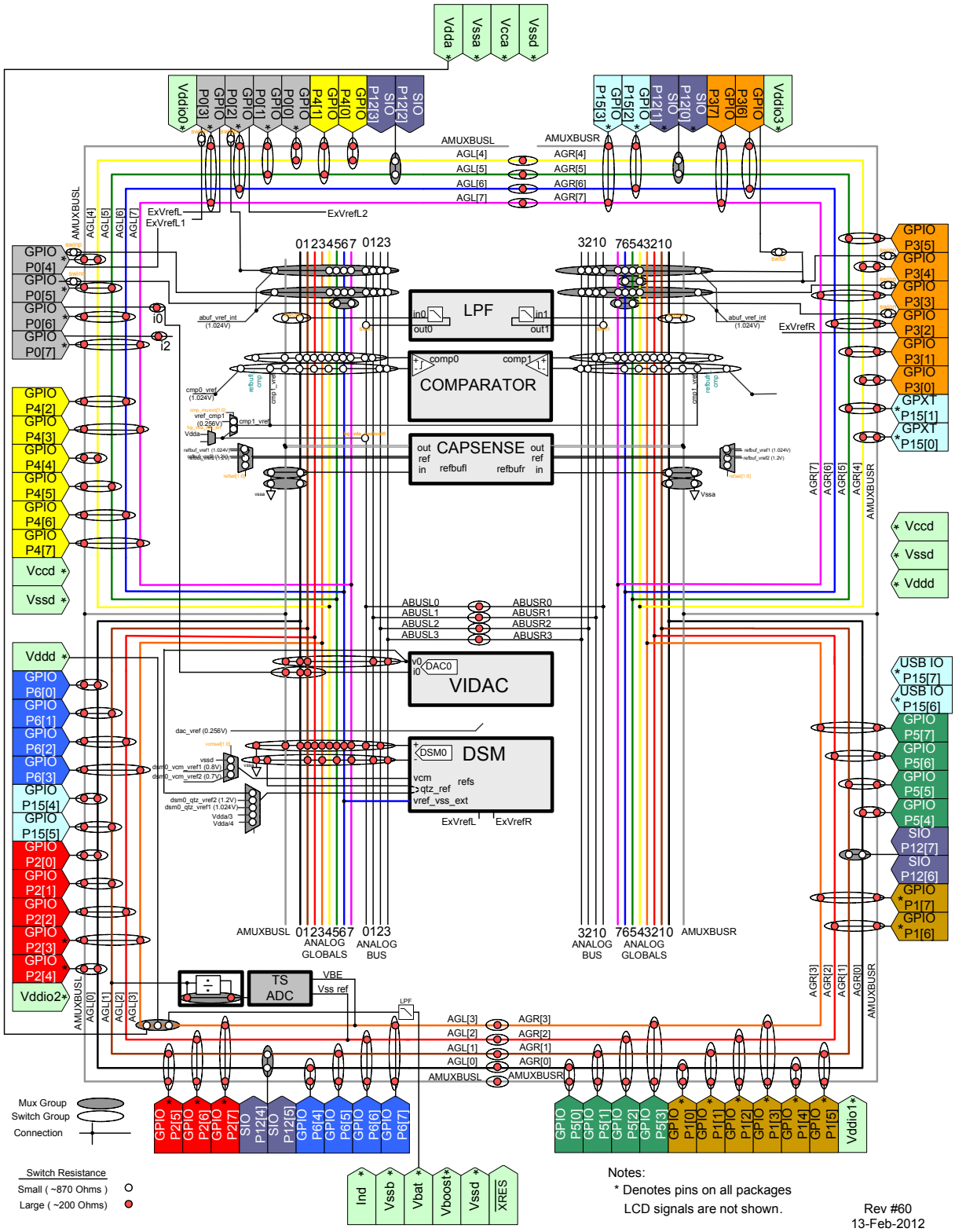
The 'Out' connection is driven from either the Digital System (when the Digital Output terminal is connected) or the Data Register (when HW connection is disabled).
The 'In' connection drives the Pin State register, and the Digital System if the Digital Input terminal is enabled and connected.
The 'An' connection connects to the Analog System.

Table 6-6. Drive Modes

Diagram	Drive Mode	PRTxDM2	PRTxDM1	PRTxDM0	PRTxDR = 1	PRTxDR = 0
0	High impedence analog	0	0	0	High Z	High Z
1	High Impedance digital	0	0	1	High Z	High Z
2	Resistive pull-up[12]	0	1	0	Res High (5K)	Strong Low
3	Resistive pull-down[12]	0	1	1	Strong High	Res Low (5K)
4	Open drain, drives low	1	0	0	High Z	Strong Low
5	Open drain, drive high	1	0	1	Strong High	High Z
6	Strong drive	1	1	0	Strong High	Strong Low
7	Resistive pull-up and pull-down[12]	1	1	1	Res High (5K)	Res Low (5K)

Note
12. Resistive pull-up and pull-down are not available with SIO in regulated output mode.

Figure 8-2. CY8C32 Analog Interconnect



To preserve detail of this figure, this figure is best viewed with a PDF display program or printed on a 11" × 17" paper.

8.4.4 LCD DAC

The LCD DAC generates the contrast control and bias voltage for the LCD system. The LCD DAC produces up to five LCD drive voltages plus ground, based on the selected bias ratio. The bias voltages are driven out to GPIO pins on a dedicated LCD bias bus, as required.

8.5 CapSense

The CapSense system provides a versatile and efficient means for measuring capacitance in applications such as touch sense buttons, sliders, proximity detection, etc. The CapSense system uses a configuration of system resources, including a few hardware functions primarily targeted for CapSense. Specific resource usage is detailed in each CapSense component in PSoC Creator.

A capacitive sensing method using a delta-sigma modulator (CSD) is used. It provides capacitance sensing using a switched capacitor technique with a delta-sigma modulator to convert the sensing current to a digital code.

8.6 Temp Sensor

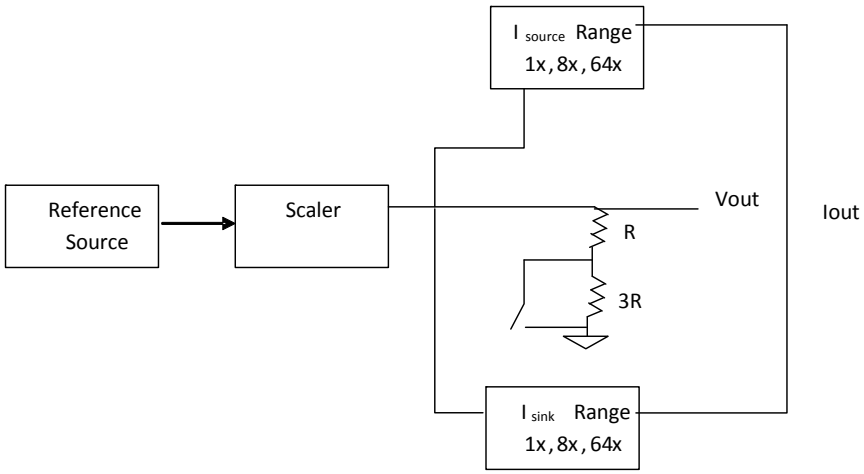
Die temperature is used to establish programming parameters for writing flash. Die temperature is measured using a dedicated sensor based on a forward biased transistor. The temperature sensor has its own auxiliary ADC.

8.7 DAC

The CY8C32 parts contain a Digital to Analog Converter (DAC). The DAC is 8-bit and can be configured for either voltage or current output. The DAC supports CapSense, power supply regulation, and waveform generation. The DAC has the following features:

- Adjustable voltage or current output in 255 steps
- Programmable step size (range selection)
- Eight bits of calibration to correct ± 25 percent of gain error
- Source and sink option for current output
- High and low speed / power modes
- 8 Msps conversion rate for current output
- 1 Msps conversion rate for voltage output
- Monotonic in nature
- Data and strobe inputs can be provided by the CPU or DMA, or routed directly from the DSI
- Dedicated low-resistance output pin for high-current mode

Figure 8-7. DAC Block Diagram



8.7.1 Current DAC

The current DAC (IDAC) can be configured for the ranges 0 to 31.875 µA, 0 to 255 µA, and 0 to 2.04 mA. The IDAC can be configured to source or sink current.

8.7.2 Voltage DAC

For the voltage DAC (VDAC), the current DAC output is routed through resistors. The two ranges available for the VDAC are 0 to 1.02 V and 0 to 4.08 V. In voltage mode any load connected to the output of a DAC should be purely capacitive (the output of the VDAC is not buffered).

Table 11-7. Recommended External Components for Boost Circuit

Parameter	Description	Conditions	Min	Typ	Max	Units
L_{BOOST}	Boost inductor	4.7 µH nominal	3.7	4.7	5.7	µH
		10 µH nominal	8.0	10.0	12.0	µH
		22 µH nominal	17.0	22.0	27.0	µH
C_{BOOST}	Total capacitance sum of V_{DDD}, V_{DDA}, V_{DDIO}[34]		17.0	26.0	31.0	µF
C_{BAT}	Battery filter capacitor		17.0	22.0	27.0	µF
I_F	Schottky diode average forward current		1.0	–	–	A
V_R	Schottky reverse voltage		20.0	–	–	V

Figure 11-8. T_A range over V_{BAT} and V_{OUT}

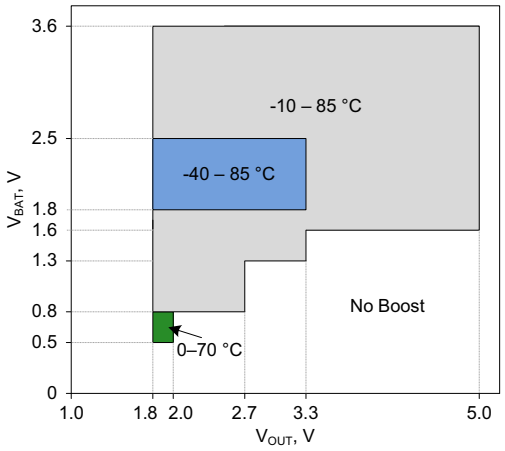


Figure 11-9. I_{OUT} range over V_{BAT} and V_{OUT}

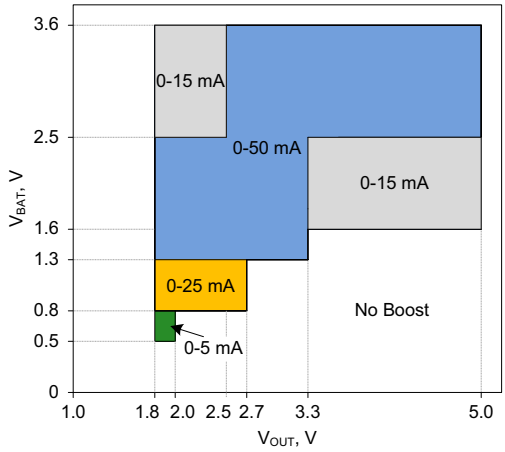
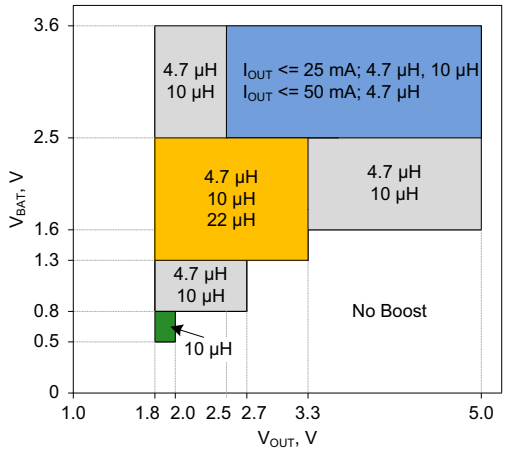


Figure 11-10. L_{BOOST} values over V_{BAT} and V_{OUT}



Note
34. Based on device characterization (Not production tested).

Figure 11-15. GPIO Output High Voltage and Current

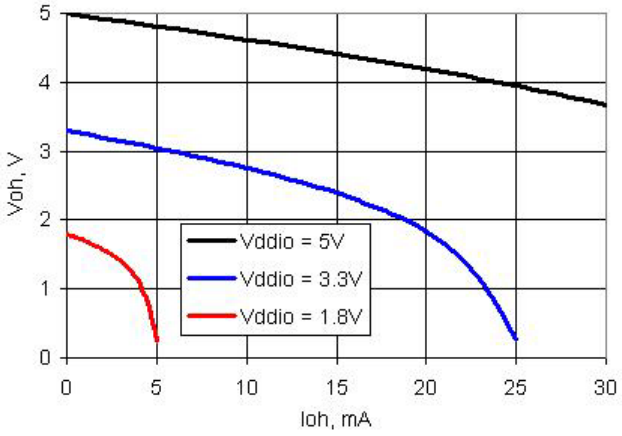


Figure 11-16. GPIO Output Low Voltage and Current

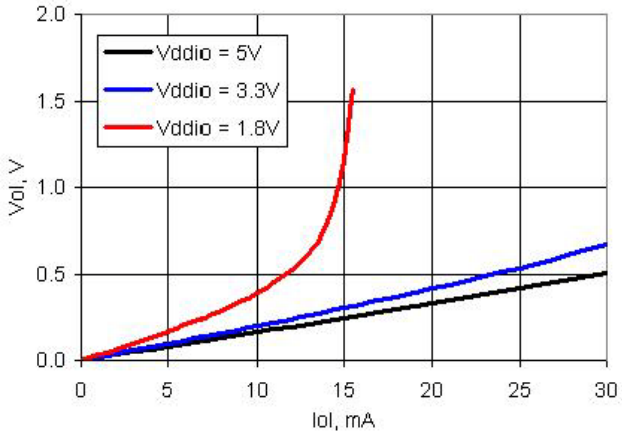


Table 11-10. GPIO AC Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
TriseF	Rise time in Fast Strong Mode[38]	3.3 V V_{DDIO} Cload = 25 pF	–	–	6	ns
TfallF	Fall time in Fast Strong Mode[38]	3.3 V V_{DDIO} Cload = 25 pF	–	–	6	ns
TriseS	Rise time in Slow Strong Mode[38]	3.3 V V_{DDIO} Cload = 25 pF	–	–	60	ns
TfallS	Fall time in Slow Strong Mode[38]	3.3 V V_{DDIO} Cload = 25 pF	–	–	60	ns
Fgpioout	GPIO output operating frequency					
	2.7 V ≤ V_{DDIO} ≤ 5.5 V, fast strong drive mode	90/10% V_{DDIO} into 25 pF	–	–	33	MHz
	1.71 V ≤ V_{DDIO} < 2.7 V, fast strong drive mode	90/10% V_{DDIO} into 25 pF	–	–	20	MHz
	3.3 V ≤ V_{DDIO} ≤ 5.5 V, slow strong drive mode	90/10% V_{DDIO} into 25 pF	–	–	7	MHz
	1.71 V ≤ V_{DDIO} < 3.3 V, slow strong drive mode	90/10% V_{DDIO} into 25 pF	–	–	3.5	MHz
Fgpioin	GPIO input operating frequency					
	1.71 V ≤ V_{DDIO} ≤ 5.5 V	90/10% V_{DDIO}	–	–	33	MHz

Note
38. Based on device characterization (Not production tested).

Figure 11-22. USBIO Output High Voltage and Current, GPIO Mode

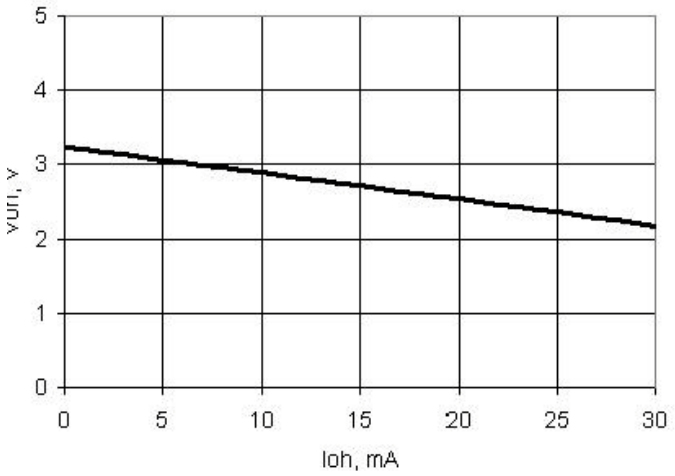


Figure 11-23. USBIO Output Low Voltage and Current, GPIO Mode

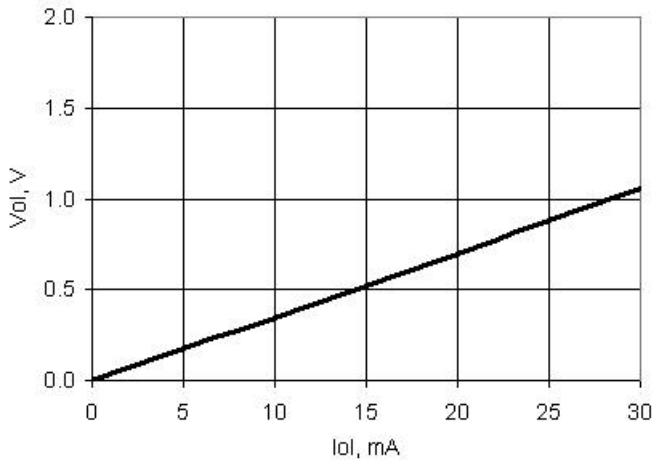


Table 11-15. USBIO AC Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
Tdrate	Full-speed data rate average bit rate		12 – 0.25%	12	12 + 0.25%	MHz
Tjr1	Receiver data jitter tolerance to next transition		–8	–	8	ns
Tjr2	Receiver data jitter tolerance to pair transition		–5	–	5	ns
Tdj1	Driver differential jitter to next transition		–3.5	–	3.5	ns
Tdj2	Driver differential jitter to pair transition		–4	–	4	ns
Tfdeop	Source jitter for differential transition to SE0 transition		–2	–	5	ns
Tfeopt	Source SE0 interval of EOP		160	–	175	ns
Tfeopr	Receiver SE0 interval of EOP		82	–	–	ns
Tfst	Width of SE0 interval during differential transition		–	–	14	ns
Fgpio_out	GPIO mode output operating frequency	3 V ≤ V_{DDD} ≤ 5.5 V	–	–	20	MHz
		V_{DDD} = 1.71 V	–	–	6	MHz
Tr_gpio	Rise time, GPIO mode, 10%/90% V_{DDD}	V_{DDD} > 3 V, 25 pF load	–	–	12	ns
		V_{DDD} = 1.71 V, 25 pF load	–	–	40	ns
Tf_gpio	Fall time, GPIO mode, 90%/10% V_{DDD}	V_{DDD} > 3 V, 25 pF load	–	–	12	ns
		V_{DDD} = 1.71 V, 25 pF load	–	–	40	ns

Figure 11-24. USBIO Output Rise and Fall Times, GPIO Mode,

11.5.2 Voltage Reference

Table 11-22. Voltage Reference Specifications

See also ADC external reference specifications in Section 11.5.1.

Parameter	Description	Conditions	Min	Typ	Max	Units
V_{REF}	Precision reference voltage	Initial trimming, 25 °C	1.014 (–1%)	1.024	1.034 (+1%)	V

11.5.3 Analog Globals

Table 11-23. Analog Globals Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
Rppag	Resistance pin-to-pin through P2[4], AGL0, DSM INP, AGL1, P2[5][49]	V_{DDA} = 3 V	–	1472	2200	Ω
Rppmuxbus	Resistance pin-to-pin through P2[3], amuxbusL, P2[4][49]	V_{DDA} = 3 V	–	706	1100	Ω

11.5.4 Comparator

Table 11-24. Comparator DC Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
V_{OS}	Input offset voltage in fast mode	Factory trim, V_{DDA} > 2.7 V, $V_{IN} \geq 0.5$ V	–		10	mV
	Input offset voltage in slow mode	Factory trim, $V_{IN} \geq 0.5$ V	–		9	mV
	Input offset voltage in fast mode[50]	Custom trim	–	–	4	mV
	Input offset voltage in slow mode[50]	Custom trim	–	–	4	mV
	Input offset voltage in ultra low-power mode	$V_{DDA} \leq 4.6$ V	–	±12	–	mV
V_{HYST}	Hysteresis	Hysteresis enable mode	–	10	32	mV
V_{ICM}	Input common mode voltage	High current / fast mode	V_{SSA}	–	V_{DDA}	V
		Low current / slow mode	V_{SSA}	–	V_{DDA}	V
		Ultra low power mode $V_{DDA} \leq 4.6$ V	V_{SSA}	–	V_{DDA} – 1.15	
CMRR	Common mode rejection ratio		–	50	–	dB
I_{CMP}	High current mode/fast mode[51]		–	–	400	µA
	Low current mode/slow mode[51]		–	–	100	µA
	Ultra low-power mode[51]	$V_{DDA} \leq 4.6$ V	–	6	–	µA

Table 11-25. Comparator AC Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
Tresp	Response time, high current mode[51]	50 mV overdrive, measured pin-to-pin	–	75	110	ns
	Response time, low current mode[51]	50 mV overdrive, measured pin-to-pin	–	155	200	ns
	Response time, ultra low-power mode[51]	50 mV overdrive, measured pin-to-pin, $V_{DDA} \leq 4.6$ V	–	55	–	µs

Notes
49. The resistance of the analog global and analog mux bus is high if $V_{DDA} \leq 2.7$ V, and the chip is in either sleep or hibernate mode. Use of analog global and analog mux bus under these conditions is not recommended
50. The recommended procedure for using a custom trim value for the on-chip comparators can be found in the TRM.
51. Based on device characterization (Not production tested).

Table 11-26. IDAC DC Specifications *(continued)*

Parameter	Description	Conditions	Min	Typ	Max	Units
I_{DD}	Operating current, code = 0	Low speed mode, source mode, range = 31.875 µA	–	44	100	µA
		Low speed mode, source mode, range = 255 µA,	–	33	100	µA
		Low speed mode, source mode, range = 2.04 mA	–	33	100	µA
		Low speed mode, sink mode, range = 31.875 µA	–	36	100	µA
		Low speed mode, sink mode, range = 255 µA	–	33	100	µA
		Low speed mode, sink mode, range = 2.04 mA	–	33	100	µA
		High speed mode, source mode, range = 31.875 µA	–	310	500	µA
		High speed mode, source mode, range = 255 µA	–	305	500	µA
		High speed mode, source mode, range = 2.04 mA	–	305	500	µA
		High speed mode, sink mode, range = 31.875 µA	–	310	500	µA
		High speed mode, sink mode, range = 255 µA	–	300	500	µA
		High speed mode, sink mode, range = 2.04 mA	–	300	500	µA

Figure 11-26. IDAC INL vs Input Code, Range = 255 µA, Source Mode

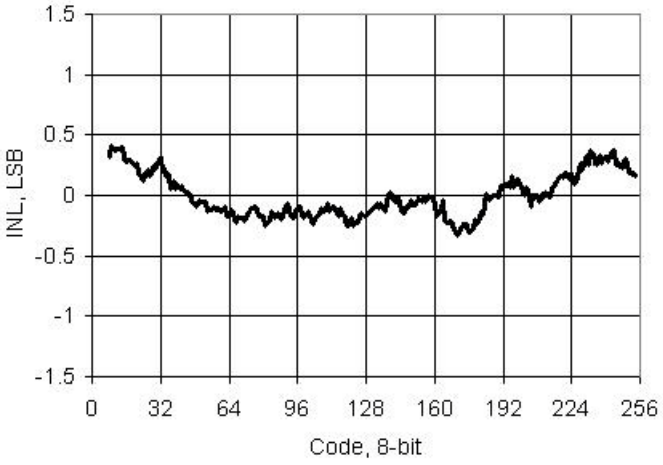


Figure 11-27. IDAC INL vs Input Code, Range = 255 µA, Sink Mode

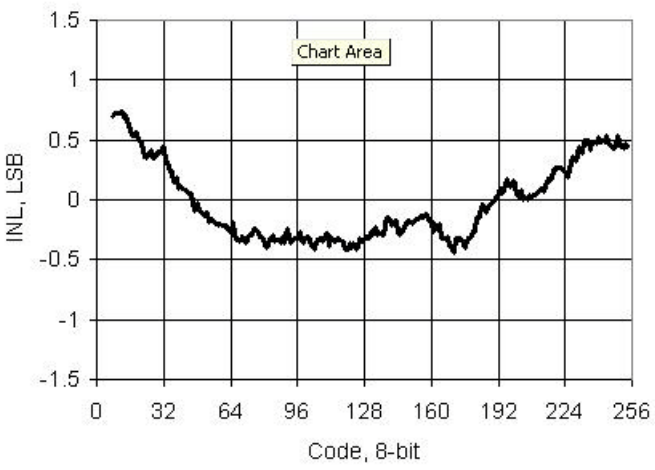


Figure 11-32. IDAC Full Scale Error vs Temperature, Range = 255 µA, Source Mode

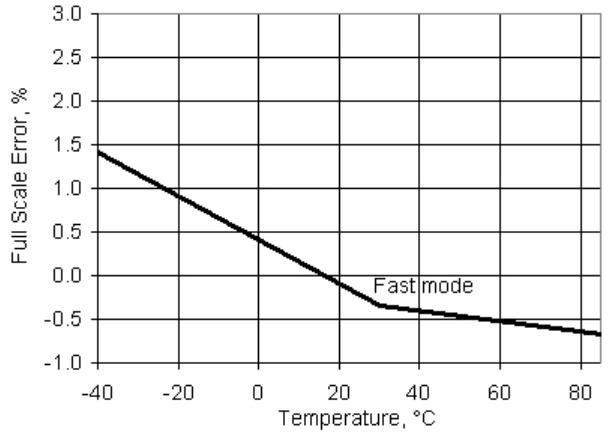


Figure 11-33. IDAC Full Scale Error vs Temperature, Range = 255 µA, Sink Mode

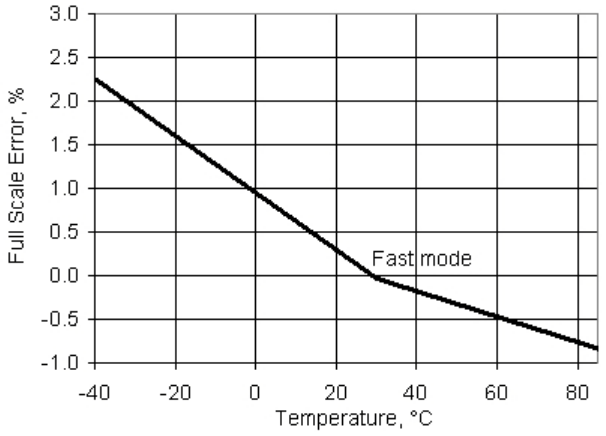


Figure 11-34. IDAC Operating Current vs Temperature, Range = 255 µA, Code = 0, Source Mode

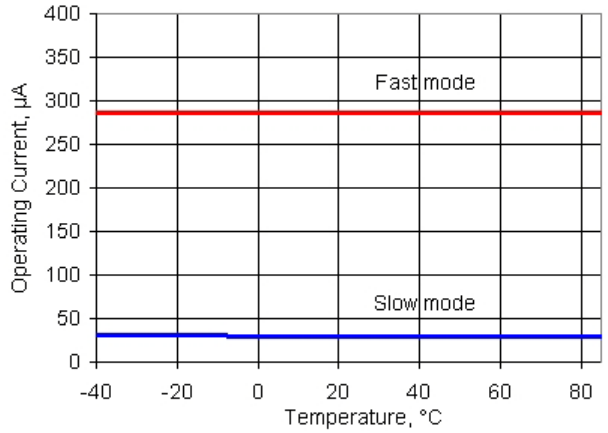


Figure 11-35. IDAC Operating Current vs Temperature, Range = 255 µA, Code = 0, Sink Mode

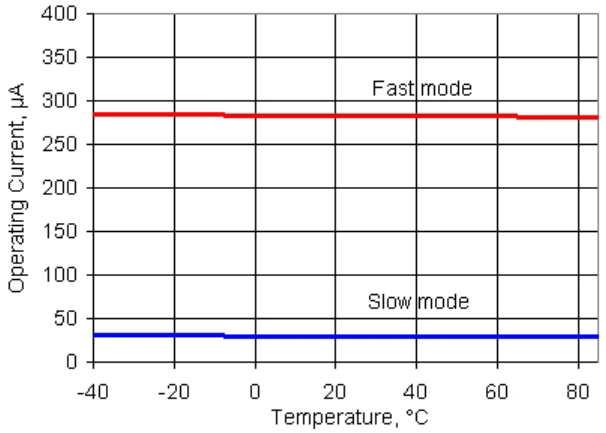


Table 11-29. VDAC AC Specifications t

Parameter	Description	Conditions	Min	Typ	Max	Units
F_{DAC}	Update rate	1 V scale	–	–	1000	ksps
		4 V scale	–	–	250	ksps
TsettleP	Settling time to 0.1%, step 25% to 75%	1 V scale, Cload = 15 pF	–	0.45	1	µs
		4 V scale, Cload = 15 pF	–	0.8	3.2	µs
TsettleN	Settling time to 0.1%, step 75% to 25%	1 V scale, Cload = 15 pF	–	0.45	1	µs
		4 V scale, Cload = 15 pF	–	0.7	3	µs
	Voltage noise	Range = 1 V, High speed mode, V_{DDA} = 5 V, 10 kHz	–	750	–	nV/sqrtHz

Figure 11-48. VDAC Step Response, Codes 0x40 - 0xC0, 1 V Mode, High speed mode, V_{DDA} = 5 V

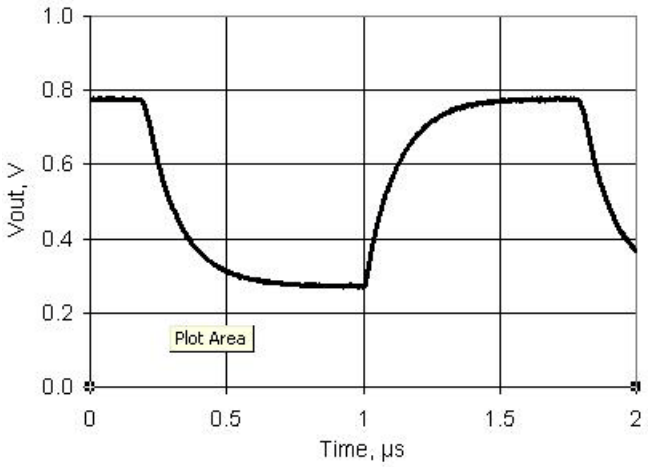


Figure 11-49. VDAC Glitch Response, Codes 0x7F - 0x80, 1 V Mode, High speed mode, V_{DDA} = 5 V

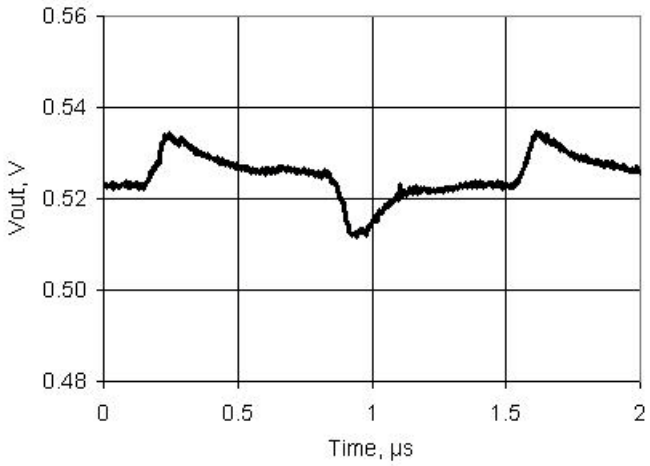


Figure 11-50. VDAC PSRR vs Frequency

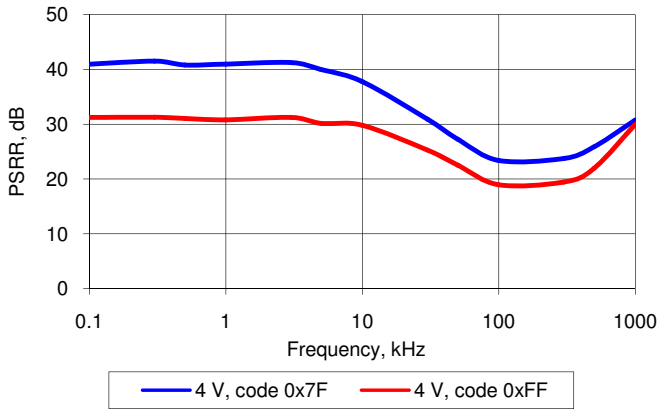
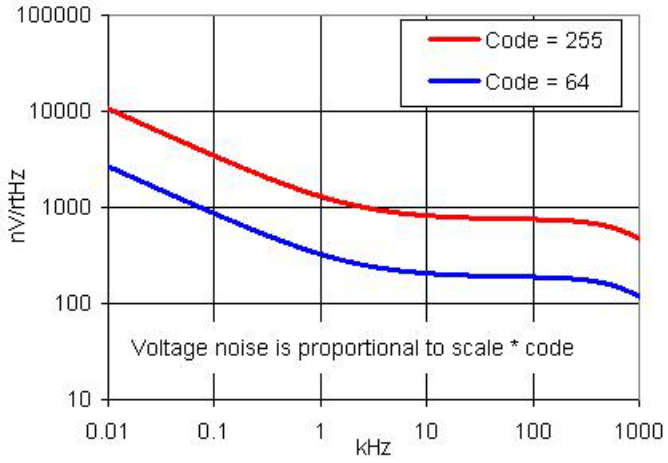


Figure 11-51. VDAC Voltage Noise, 1 V Mode, High speed mode, V_{DDA} = 5 V



11.5.7 Temperature Sensor

Table 11-30. Temperature Sensor Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
	Temp sensor accuracy	Range: –40 °C to +85 °C	–	±5	–	°C

11.5.8 LCD Direct Drive

Table 11-31. LCD Direct Drive DC Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
I_{CC}	LCD system operating current	Device sleep mode with wakeup at 400-Hz rate to refresh LCDs, bus clock = 3 MHz, $V_{DDIO} = V_{DDA} = 3$ V, 4 commons, 16 segments, 1/4 duty cycle, 50 Hz frame rate, no glass connected	–	38	–	µA
I_{CC_SEG}	Current per segment driver	Strong drive mode	–	260	–	µA
V_{BIAS}	LCD bias range (V_{BIAS} refers to the main output voltage(V0) of LCD DAC)	$V_{DDA} \geq 3$ V and $V_{DDA} \geq V_{BIAS}$	2	–	5	V
	LCD bias step size	$V_{DDA} \geq 3$ V and $V_{DDA} \geq V_{BIAS}$	–	9.1 × V_{DDA}	–	mV
	LCD capacitance per segment/common driver	Drivers may be combined	–	500	5000	pF
	Long term segment offset		–	–	20	mV
I_{OUT}	Output drive current per segment driver)	V_{DDIO} = 5.5V, strong drive mode	355	–	710	µA

Table 11-32. LCD Direct Drive AC Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
f_{LCD}	LCD frame rate		10	50	150	Hz

11.8.5 SWD Interface

Figure 11-58. SWD Interface Timing

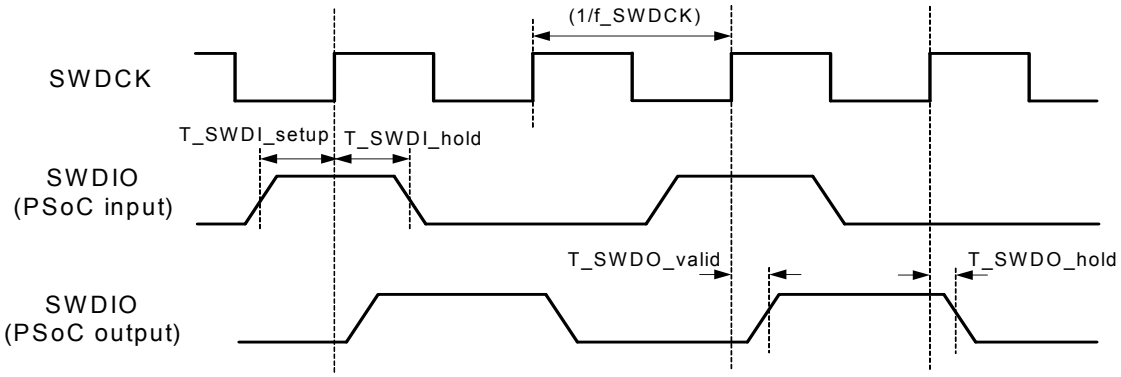


Table 11-63. SWD Interface AC Specifications[67]

Parameter	Description	Conditions	Min	Typ	Max	Units
f_SWDCK	SWDCLK frequency	3.3 V ≤ V_{DDD} ≤ 5 V	–	–	14[68]	MHz
		1.71 V ≤ V_{DDD} < 3.3 V	–	–	7[68]	MHz
		1.71 V ≤ V_{DDD} < 3.3 V, SWD over USBIO pins	–	–	5.5[68]	MHz
T_SWDI_setup	SWDIO input setup before SWDCK high	T = 1/f_SWDCK max	T/4	–	–	
T_SWDI_hold	SWDIO input hold after SWDCK high	T = 1/f_SWDCK max	T/4	–	–	
T_SWDO_valid	SWDCK high to SWDIO output	T = 1/f_SWDCK max	–	–	2T/5	

11.8.6 SWV Interface

Table 11-64. SWV Interface AC Specifications[30]

Parameter	Description	Conditions	Min	Typ	Max	Units
	SWV mode SWV bit rate		–	–	33	Mbit

11.9 Clocking

Specifications are valid for –40 °C ≤ T_A ≤ 85 °C and T_J ≤ 100 °C, except where noted. Specifications are valid for 1.71 V to 5.5 V, except where noted.

11.9.1 Internal Main Oscillator

Table 11-65. IMO DC Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
	Supply current					
	24 MHz – USB mode	With oscillator locking to USB bus	–	–	500	µA
	24 MHz – non USB mode		–	–	300	µA
	12 MHz		–	–	200	µA
	6 MHz		–	–	180	µA
	3 MHz		–	–	150	µA

Notes
67. Based on device characterization (Not production tested).
68. f_SWDCK must also be no more than 1/3 CPU clock frequency.